

## 650 V Power SiC Merged PIN Schottky Diode, 6 A



PRIMARY CHARACTERISTICS			
I <sub>F(AV)</sub>	6 A		
V <sub>R</sub>	650 V		
V <sub>F</sub> at I <sub>F</sub> at 150 °C	1.70 V		
T <sub>J</sub> max.	175 °C		
I <sub>R</sub> at V <sub>R</sub> at 175 °C	4.4 µA		
Q <sub>C</sub> (V <sub>R</sub> = 400 V)	17 nC		
Package	2L TO-220AC		
Circuit configuration	Single		

#### **FEATURES**

 Majority carrier diode using Schottky technology on SiC wide band gap material



- Positive V<sub>F</sub> temperature coefficient for easy paralleling
- · Virtually no recovery tail and no switching losses
- Temperature invariant switching behavior
- 175 °C maximum operating junction temperature
- MPS structure for high ruggedness to forward current surge events
- Meets JESD 201 class 1A whisker test
- Solder bath temperature 275 °C maximum, 10 s per JESD 22-B106
- Material categorization: for definitions of compliance please see <a href="https://www.vishav.com/doc?99912"><u>www.vishav.com/doc?99912</u></a>

#### **DESCRIPTION / APPLICATIONS**

Wide band gap SiC based 650 V Schottky diode, designed for high performance and ruggedness.

Optimum choice for high speed hard switching and efficient operation over a wide temperature range, it is also recommended for all applications suffering from Silicon ultrafast recovery behavior.

Typical applications include AC/DC PFC and DC/DC ultra high frequency output rectification in FBPS and LLC converters.

#### **MECHANICAL DATA**

Case: 2L TO-220AC

Molding compound meets UL 94 V-0 flammability rating Base P/N-M3 - halogen-free, RoHS-compliant

Terminals: matte tin plated leads, solderable per

J-STD-002 and JESD 22-B102

Mounting torque: 10 in-lbs maximum

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C unless otherwise specified)					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Peak repetitive reverse voltage	$V_{RRM}$		650	V	
Average rectified forward current	I <sub>F(AV)</sub>	T <sub>C</sub> = 127 °C (DC)	6	Α	
DC blocking voltage	$V_{DC}$		650	V	
Repetitive peak surge current	I <sub>FRM</sub>	$T_C$ = 25 °C, f = 50 Hz, square wave, DC = 25 %	23		
Non-repetitive peak forward surge current	I <sub>FSM</sub>	$T_C = 25$ °C, $t_p = 10$ ms, half sine wave	39	Α	
		$T_C = 110 ^{\circ}\text{C}$ , $t_p = 10 \text{ms}$ , half sine wave	37		
Power dissipation	P <sub>tot</sub> (1)	T <sub>C</sub> = 25 °C	42	W	
		T <sub>C</sub> = 110 °C	18	] <sup>vv</sup>	
l <sup>2</sup> t value	∫i <sup>2</sup> dt	T <sub>C</sub> = 25 °C	8	A <sup>2</sup> s	
		T <sub>C</sub> = 110 °C	6.8		
Operating junction and storage temperatures	T <sub>J</sub> <sup>(2)</sup> , T <sub>Stg</sub>		-55 to +175	°C	

#### Notes

<sup>(1)</sup> Based on maximum Rth

 $<sup>^{(2)}</sup>$  The heat generated must be less than the thermal conductivity from junction-to-ambient:  $dP_D/dT_J < 1/R_{\theta JA}$ 



<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
		I <sub>F</sub> = 6 A	-	1.45	1.70		
Forward voltage	V <sub>F</sub>	I <sub>F</sub> = 6 A, T <sub>J</sub> = 150 °C	-	1.70	2.10	V	
		I <sub>F</sub> = 6 A, T <sub>J</sub> = 175 °C	-	1.80	-		
Reverse leakage current I <sub>R</sub>	I <sub>R</sub>	$V_R = V_R$ rated	-	-	35		
		V <sub>R</sub> = V <sub>R</sub> rated, T <sub>J</sub> = 150 °C	-	-	75	μΑ	
		V <sub>R</sub> = V <sub>R</sub> rated, T <sub>J</sub> = 175 °C	-	4.4	-		
Total capacitance	С	V <sub>R</sub> = 1 V, f = 1 MHz	-	250	-	nE	
		V <sub>R</sub> = 400 V, f = 1 MHz	-	27	-	pF	
Total capacitive charge	Q <sub>C</sub>	V <sub>R</sub> = 400 V, f = 1 MHz	-	17	-	nC	

THERMAL - MECHANICAL SPECIFICATIONS (T <sub>A</sub> = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Thermal resistance, junction-to-case	R <sub>thJC</sub>		-	2.55	3.6	°C/W
Marking device				C06E	T07T	

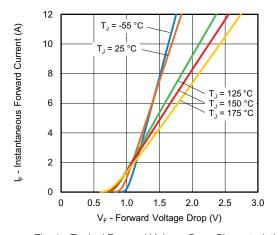


Fig. 1 - Typical Forward Voltage Drop Characteristics

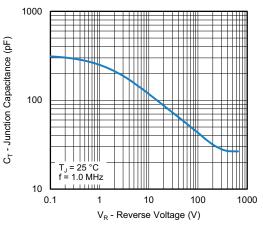


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

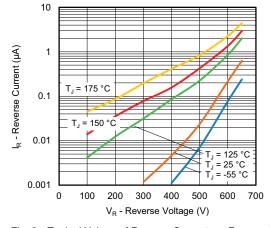


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

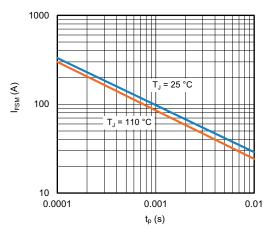


Fig. 4 - Non-Repetitive Peak Forward Surge Current vs. Pulse Duration (Square Wave)

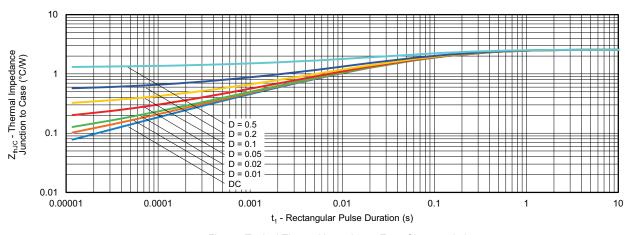


Fig. 5 - Typical Thermal Impedance  $Z_{\text{thJC}}$  Characteristics

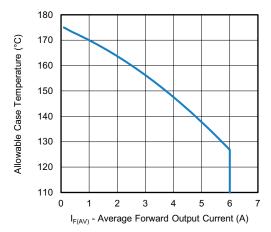


Fig. 6 - Maximum Allowable Case Temperature vs. Average Forward Current

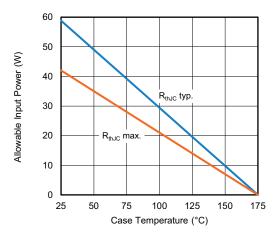


Fig. 7 - Forward Power Loss Characteristics

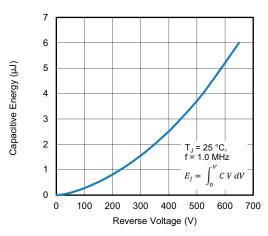


Fig. 8 - Typical Capacitive Energy vs. Reverse Voltage

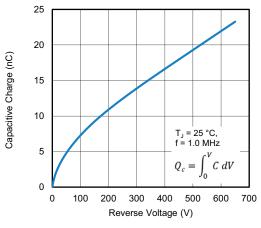
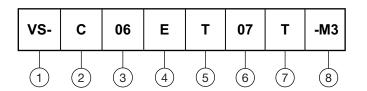


Fig. 9 - Typical Capacitive Charge vs. Reverse Voltage



### **ORDERING INFORMATION TABLE**

**Device code** 



1 - Vishay Semiconductors product

- C = SiC diode

3 - Current rating (06 = 6 A)

- E = single diode

5 - Package TO-220

**6** - Voltage rating: (07 = 650 V)

**7** - T = true 2 pin

8 - Environmental digit:

-M3 = halogen-free, RoHS-compliant, and termination lead (Pb)-free

ORDERING INFORMATION					
PREFERRED P/N	BASE QUANTITY	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION		
VS-C06ET07T-M3	50/tube	1000	Antistatic plastic tubes		

LINKS TO RELATED DOCUMENTS				
Dimensions <u>www.vishay.com/doc?96069</u>				
Part marking information	www.vishay.com/doc?95391			



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